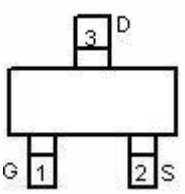
P-Ch 20V Fast Switching MOSFETS

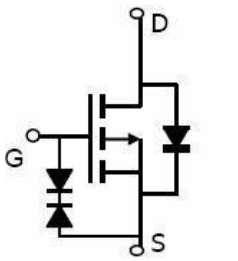
Product Summary

BVDSS	RDSON	ID
-20V	36mΩ	- 4A



Marking and pin Assignment

SOT-23 top view



- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-20		V
V_{GS}	Gate-Source Voltage	±10		V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ -4.5V[1]	-4.2	-4	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ -4.5V[1]	-4	-3.7	A
I_{DM}	Pulsed Drain Current[2]	-18		A
P_D@T_A=25°C	Total Power Dissipation[3]	1.32	1	W
T_{STG}	Storage Temperature Range	-55 to 150		°C
T_J	Operating Junction Temperature Range	-55 to 150		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	125	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	---	95	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	80	°C/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= -250μA	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±10V	-	-	±10	uA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.4	-0.7	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =-4.5V, I_D =-4A	-	30	40	mΩ
		V_{GS} =-2.5V, I_D =-3A	-	40	56	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz	-	289	-	pF
C_{oss}	Output Capacitance		-	98	-	pF
C_{rss}	Reverse Transfer Capacitance		-	22	-	pF
Q_g	Total Gate Charge	V_{DS} = -10V, I_D = -4.1A, V_{GS} = -4.5V	-	9	-	nC
Q_{gs}	Gate-Source Charge		-	1	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	2.6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -10V, R_G = 1Ω, V_{GEN}=-4.5V,R_L=1.2Ω	-	12	-	ns
t_r	Turn-on Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	30	-	ns
t_f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-4.1	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-16.4	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -4.1A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

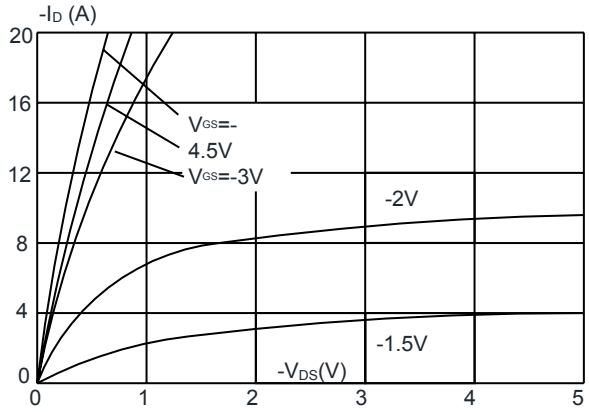


Figure 2: Typical Transfer Characteristics

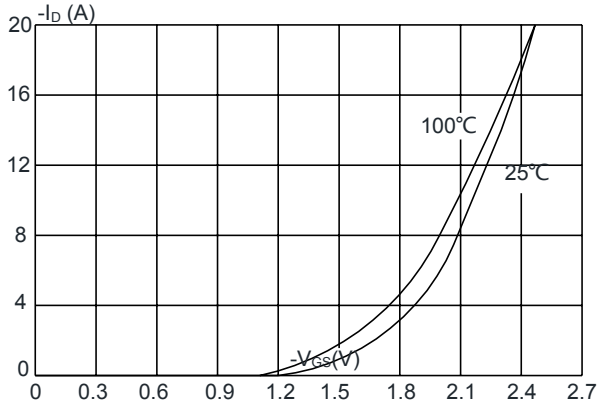


Figure 3: On-resistance vs. Drain Current

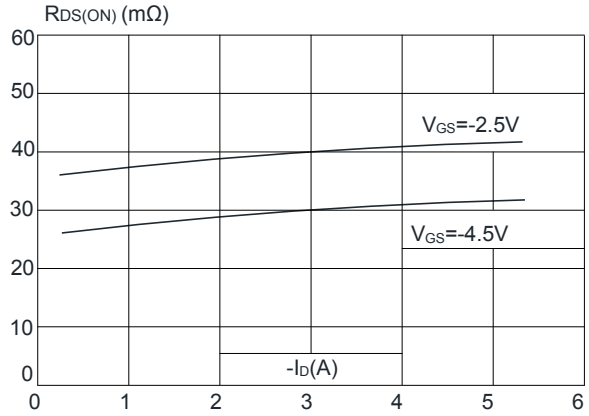


Figure 4: Body Diode Characteristics

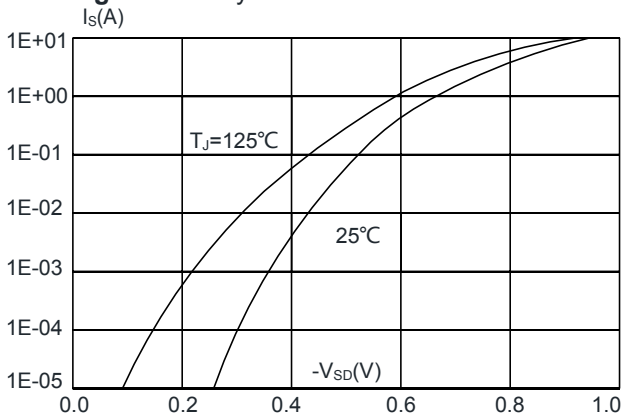


Figure 5: Gate Charge Characteristics

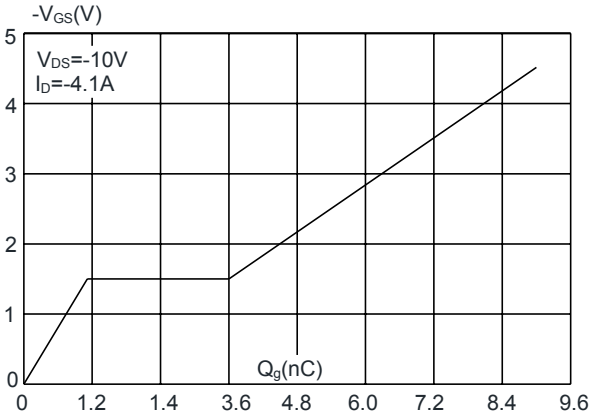


Figure 6: Capacitance Characteristics

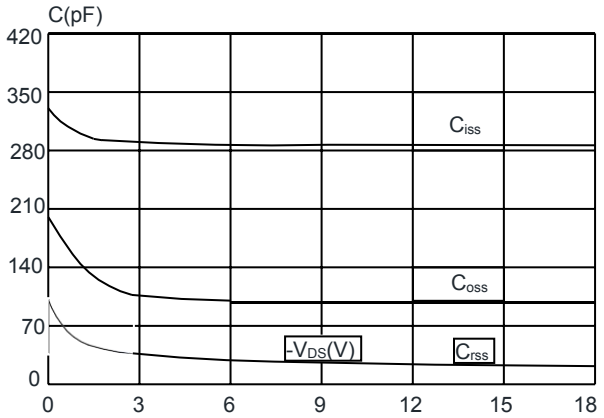


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

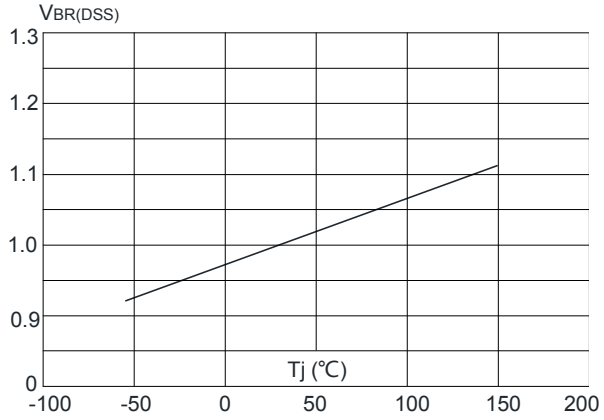


Figure 8: Normalized on Resistance vs. Junction Temperature

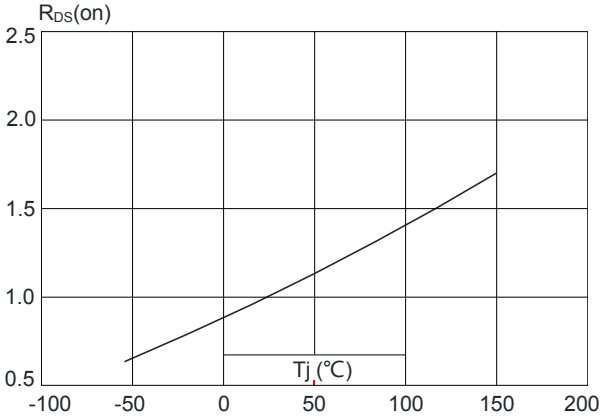


Figure 9: Maximum Safe Operating Area

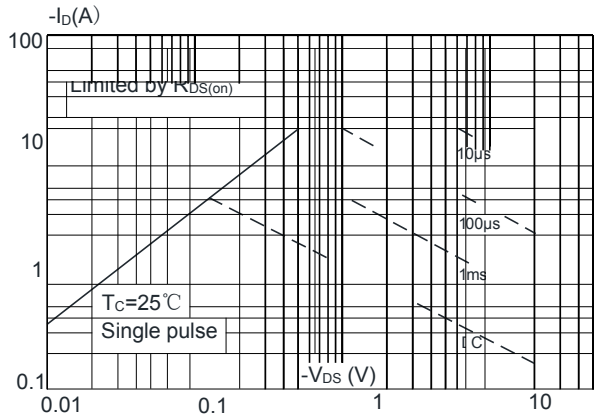


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

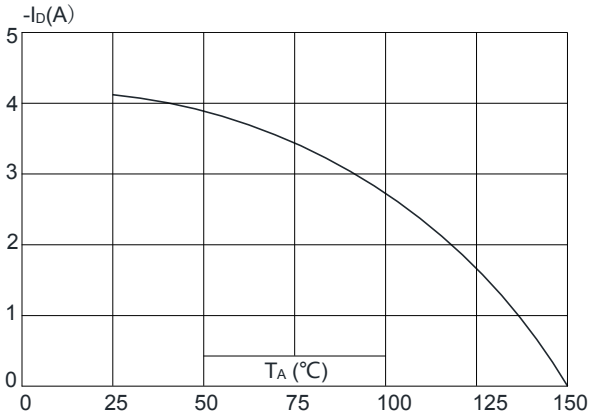
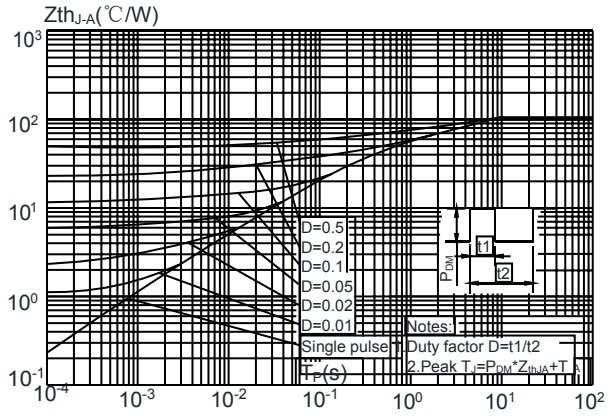
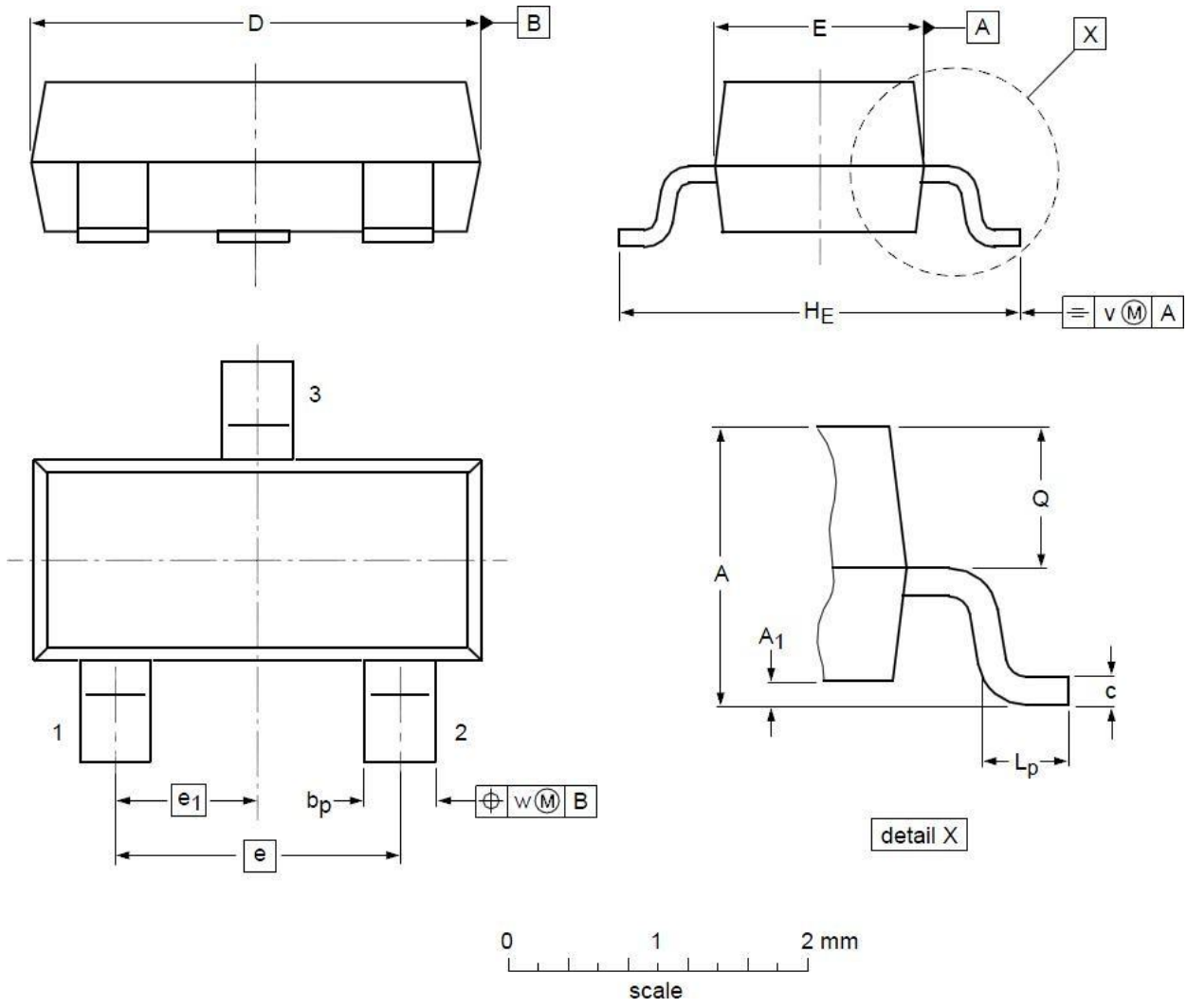


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOT-23 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	**A_1**	0.01	0.05	0.10
b_p	0.30	0.42	0.50	**c**	0.08	0.13	0.15
D	2.80	2.92	3.00	**E**	1.20	1.33	1.40
e	--	1.90	--	**e_1**	--	0.95	--
H_E	2.25	2.40	2.55	**L_p**	0.30	0.42	0.50
Q	0.45	0.49	0.55	**v**	--	0.20	--
w	--	0.10	--				

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